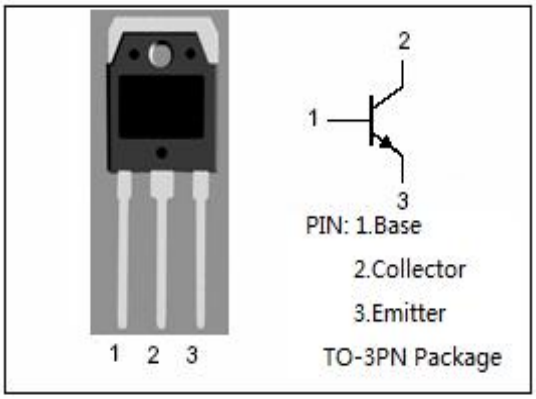
isc Silicon NPN Power Transistor — 2SD847

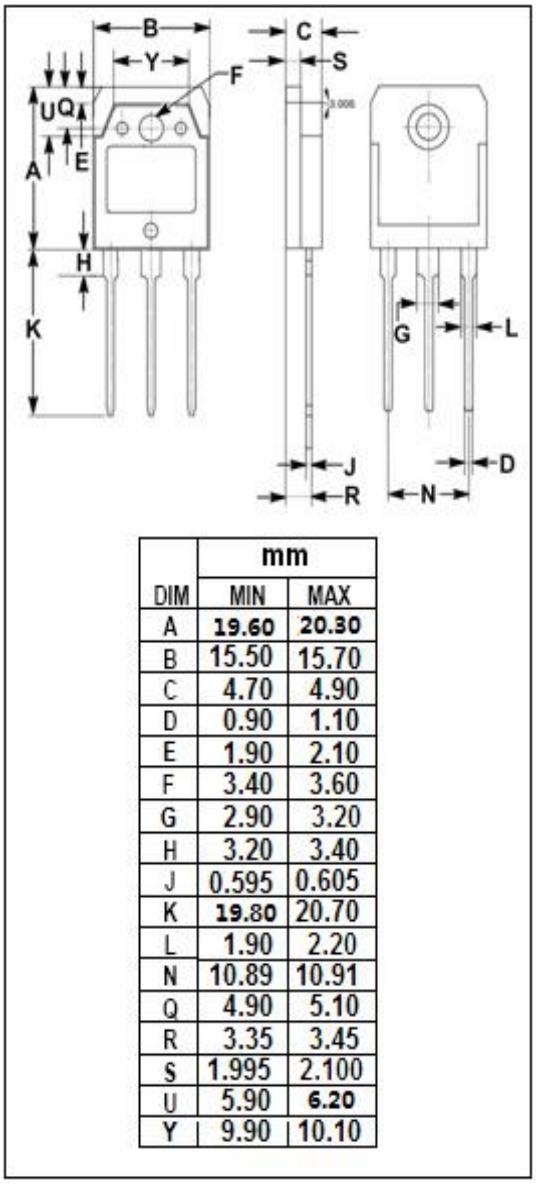
DESCRIPTION

- Good Linearity of h_{FE}
- High Collector Current
- Wide Area of Safe Operation
- High Reliability
- Complement to Type 2SB757
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Audio amplifier applications
- Series regulators applications
- General purpose power amplifiers



DIM	mm MIN	MAX
A	**19.60**	**20.30**
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	**19.80**	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	**6.20**
Y	9.90	10.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base voltage	5	V
I_C	Collector Current-Continuous	15	A
I_B	Base Current-Continuous	5	A
P_C	Collector Power Dissipation @ T_C=25℃	80	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.56	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA ; I_B= 0	40			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 0.1mA ; I_E= 0	40			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 0.1mA ; I_C= 0	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 5A; I_B= 0.5A			0.8	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 5A; I_B= 0.5A			1.8	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 40V ; I_E= 0			0.01	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			0.1	mA
h_{FE}	DC Current Gain	I_C= 5A ; V_{CE}= 2V	40		240	
Switching times						
t_{on}	Turn-on Time	I_C= 15A , I_{B1}= I_{B2}= 1.5A R_L= 2Ω ;P_W=20μs Duty Cycle≤2%			1.0	μs
t_{stg}	Storage Time				2.0	μs
t_f	Fall Time				1.0	μs